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Models for IC Buffers: A Top-down Approach

Taking the nonlinear Thévenin-like topology beyond the proof of concept

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Outline

- Context
- Building a nonlinear Thévenin-like model for IC buffers
- Demonstrating the approach on a TI driver
- Discussing the implementation
- $_{\rm O}$ Extending the model to account for $v_{\rm dd}$ variations
- Conclusion





Context

Joint research on buffer modeling

Politecnico di Torino, Italy and Université de Brest, France





Focus:

- New methodologies and approaches to IC buffer macromodeling
- Better accuracy in critical conditions, more general approach to modeling
- Particular focus on <u>overclocking</u>: issue present in literature, conferences and IBIS summit meetings







➤ General idea presented at the IBIS Summit Meeting in 2013

NEW!

Implementation details for every block

Extraction: full walkthrough

➤Accounting for V_{DD} variation







Example: Texas Instruments driver SN74ALVCH16973, VDD = 2,5V







OPEN CIRCUIT VOLTAGE

Single-input-single-output nonlinear element
 Gives the input-output characteristic of the driver
 Can be modeled in different ways









OPEN CIRCUIT VOLTAGE

Hammerstein structure (well known in control-theory)
 Static bloc: Step like function, table-based implementation
 Linear filter identified via vector fitting
 Delay modeled by ideal transmission line





OPEN CIRCUIT VOLTAGE

 Very accurate model using very simple and robust structure
 Dynamic elements could be added if needed

NMSE =
$$10\log_{10} \frac{\sum_{k=0}^{K-1} (y_{ref}(k) - y_{approx}(k))^2}{\sum_{k=0}^{K-1} (y_{ref}(k))^2}$$

NMSE gives a measure of the accuracy over a finite number of samples K.



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NONLINEAR CONDUCTANCE

On state / off state separationStatic table based model at this stage



$$G(v_1, v_2) = \left[\hat{e}(v_1) / V_{DD}\right] G_H(v_2) + \left[\left(1 - \hat{e}(v_1)\right) / V_{DD}\right] G_L(v_2)$$

= $\widetilde{w}_H G_H(v_2) + \widetilde{w}_L G_L(v_2)$













Relation with IBIS

Thévenin-like

$$i_{2}(t) = G(v_{1}, v_{2})[\hat{e}(v_{1}) - v_{2}]$$

$$= [(\hat{e}(v_{1})/V_{DD})G_{H}(v_{2}) + ((1 - \hat{e}(v_{1}))/V_{DD})G_{L}(v_{2})][\hat{e}(v_{1}) - v_{2}]$$

$$= [\widetilde{w}_{H}G_{H}(v_{2}) + \widetilde{w}_{L}G_{L}(v_{2})][\hat{e}(v_{1}) - v_{2}]$$

$$= \widetilde{w}_{H}[\hat{e}(v_{1}) - v_{2}]G_{H}(v_{2}) + \widetilde{w}_{L}[\hat{e}(v_{1}) - v_{2}]G_{L}(v_{2})$$

$$= \widetilde{w}_{H}\widetilde{f}_{H}(v_{1}, v_{2}) + \widetilde{w}_{L}\widetilde{f}_{L}(v_{1}, v_{2})$$
IBIS-like

$$i_{2}(t) = w_{H}f_{H}(V_{DD} - v_{2}) + w_{L}f_{L}(v_{2})$$

Static characteristics of the output port in high and low state

>Weighting functions computed from devices responses on two resistive loads





Relation with IBIS

Thévenin-like

$$i_{2}(t) = G(v_{1}, v_{2})[\hat{e}(v_{1}) - v_{2}]$$

$$= [(\hat{e}(v_{1})/V_{DD})G_{H}(v_{2}) + ((1 - \hat{e}(v_{1}))/V_{DD})G_{L}(v_{2})][\hat{e}(v_{1}) - v_{2}]$$

$$= [\widetilde{w}_{H}G_{H}(v_{2}) + \widetilde{w}_{L}G_{L}(v_{2})][\hat{e}(v_{1}) - v_{2}]$$

$$= \widetilde{w}_{H}[\hat{e}(v_{1}) - v_{2}]G_{H}(v_{2}) + \widetilde{w}_{L}[\hat{e}(v_{1}) - v_{2}]G_{L}(v_{2})$$

$$= \widetilde{w}_{H}\widetilde{f}_{H}(v_{1}, v_{2}) + \widetilde{w}_{L}\widetilde{f}_{L}(v_{1}, v_{2})$$
IBIS-like

$$i_{2}(t) = w_{H}f_{H}(V_{DD} - v_{2}) + w_{L}f_{L}(v_{2})$$

In the Thévenin-like model both $\tilde{w}_{H,L}$ and $\tilde{f}_{H,L}$ depend on v_1 In the IBIS-like model only $w_{H,L}$ depend on v_1







Transient simulation results









Transient simulation results



Overclocking: solve a problem or solve the problem ?





Transient simulation results





Summing things up...



Tables + Simple filter + delay

Static table-based model here → dynamic models: compensation capacitance, linear FIR, nonlinear model if needed







Summing things up...



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Summing things up...



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Accounting for Vdd variation





Conclusion

Top down approach: circuit theory → macromodel.
Easy implementation.
Basic building block for future EDA tools.
Good potential in solving inaccuracies related to jitter, overclocking, etc.

References:

Conference paper : C. Diouf, M. Telescu , N. Tanguy, I.S. Stievano, F.G. Canavero, "Robust nonlinear models for CMOS buffers", 20th IEEE Workshop on Signal and Power Integrity, May 2016, Turin, taly *Extended paper:* C. Diouf, M. Telescu, I. S. Stievano, N. Tanguy, F. G. Canavero, "Simplified topology for IC buffer behavioural models", IET Circuits, Devices & Systems, 2016 (in press).



